Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT404 (D2PAK) surface mountable plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{i(max)} = 150$ °C).

2. Features and benefits

- High bidirectional blocking voltage capability
- High junction operating temperature capability
- · High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- · Very high current surge capability

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- · Inrush protection
- Motor control
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{T(AV)}	average on-state current	half sine wave; $T_{mb} \le 129 ^{\circ}\text{C}$; Fig. 1		-	-	12.7	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 129 ^{\circ}\text{C}$; Fig. 2; Fig. 3		-	-	20	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5		-	-	210	Α
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$		-	-	231	Α
Tj	junction temperature			-	-	150	°C
Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 7$		-	4.5	32	mA
Dynamic characteristics							

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	A -
2	Α	anode		G sym037
3	G	gate		<u> </u>
mb	Α	mounting base; connected to anode		
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
TYN20B-600T	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

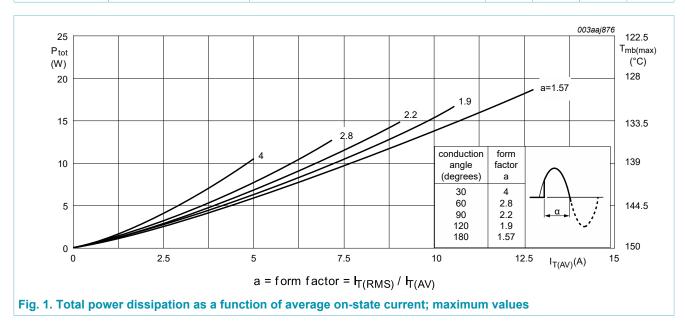
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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
V_{RRM}	repetitive peak reverse voltage		-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 129 °C; <u>Fig. 1</u>	-	12.7	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 129 ^{\circ}\text{C}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$	-	20	А
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; Fig. 4; Fig. 5	-	210	A
		half sine wave; T _{j(init)} = 25 °C; t _p = 8.3 ms	-	231	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	220.5	A²s
dl _T /dt	rate of rise of on-state current	I _G = 70 mA	-	100	A/µs
I _{GM}	peak gate current		-	5	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
P _{G(AV)}	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C



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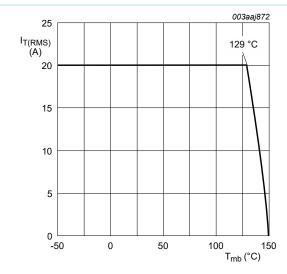


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

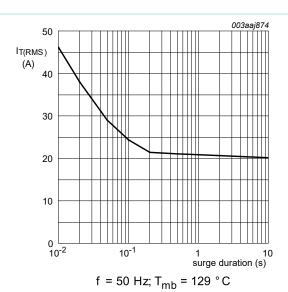


Fig. 3. RMS on-state current as a function of surge duration; maximum values

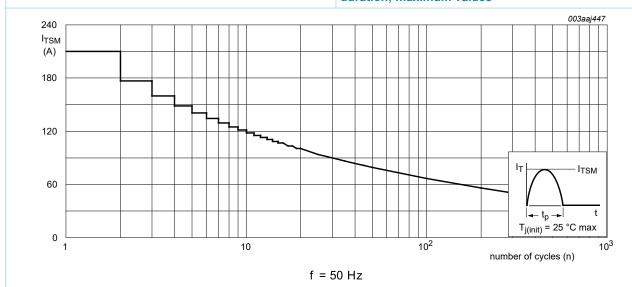
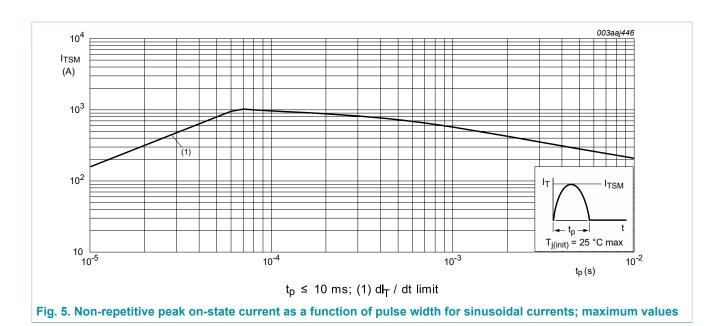


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 6	-	-	1.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	minimum footprint, FR4 board	-	55	-	K/W

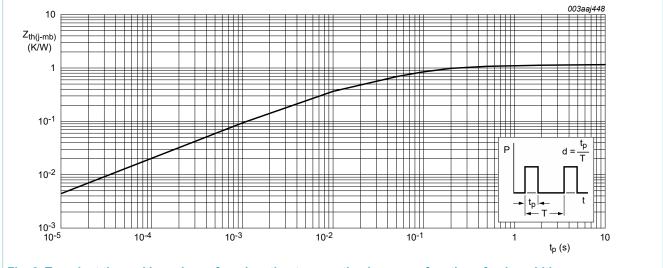


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

6 / 12

SCR

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	M	n T	yp	Max	Unit
Static chara	acteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	-	4	.5	32	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 8$	-	2	1	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	1	6	40	mA
V_T	on-state voltage	I _T = 32 A; T _j = 25 °C; <u>Fig. 10</u>	-	1	.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0	.7	1.3	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; Fig. 11	0.3	2 0	.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0	.2	1	mA
I _R	reverse current	V _R = 600 V; T _j = 150 °C	-	0	.2	1	mA
Dynamic ch	naracteristics						
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	10	00 -		-	V/µs

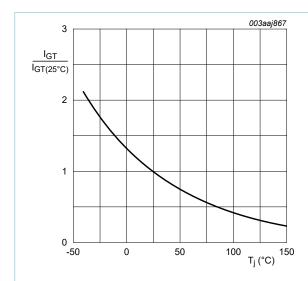


Fig. 7. Normalized gate trigger current as a function of junction temperature

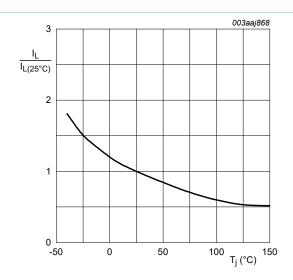


Fig. 8. Normalized latching current as a function of junction temperature

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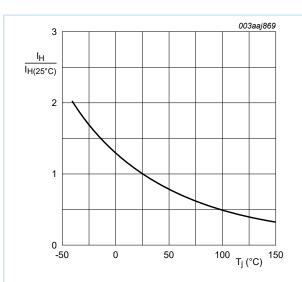
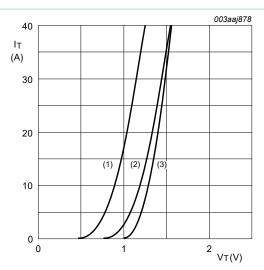


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.0485 V; R_s = 0.0133 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

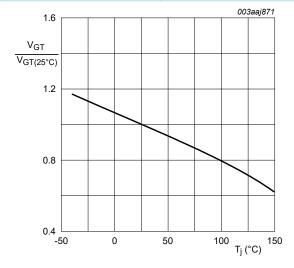
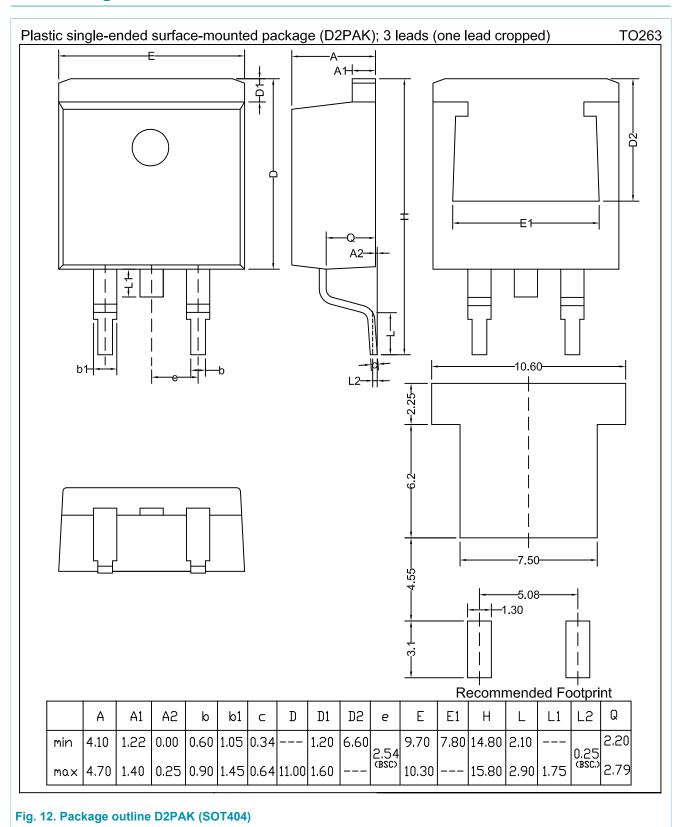


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

8 / 12

10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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12. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	3
8.	Thermal characteristics	6
9.	Characteristics	7
10.	Package outline	9
11	Legal information	10

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